

ESD1P0RF...

RF ESD Protection Diodes

- ESD / transient protection of RF antenna / interfaces or ultra high speed data lines acc. to: IEC61000-4-2 (ESD): ± 20 kV (contact) IEC61000-4-4 (EFT): 40 A (5/50 ns) IEC61000-4-5 (surge): 10 A (8/20 µs)
- Ultra low capacitance of 1 pF typ. (0.5 pF per diode)
- Low clamping voltage
- Pb-free (ROHS compliant) package

Applications in anti-parallel configuration

• For low RF signal levels without superimposed DC voltage: e.g. GPS, WLAN, Bluetooth

Applications in rail-to-rail configuration

 For high RF signal levels or low RF signal levels with superimposed DC voltage: e.g. HDMI, S-ATA, Gbit Ethernet



ESD1P0RFW

ESD1P0RFS





Туре	Package	Configuration	Marking
ESD1P0RFS	SOT363	2 channels	E6s
ESD1P0RFW	SOT323	1 channel	E6s





Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit				
ESD contact discharge ¹⁾	V _{ESD}	20	kV				
Peak pulse current ($t_p = 8 / 20 \ \mu s$) ²⁾	I _{pp}	10	A				
Operating temperature range	T _{op}	-55150	°C				
Storage temperature	T _{stg}	-65150					

Electrical Characteristics at $T_A = 25^{\circ}C$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Reverse working voltage ³⁾	V _{RWM}	-	-	70	V
Reverse current	I _R	-	-	100	nA
V _R = 70 V					
Forward clamping voltage ²⁾	V _{FC}				V
I _{PP} = 3 A, t _p = 8/20 μs		-	4	7	
$I_{\rm PP}$ = 10 A, $t_{\rm p}$ = 8/20 µs		-	12	15	
Line capacitance ⁴⁾	CT				pF
$V_{\rm R} = 0 {\rm V}, f = 1 {\rm MHz}$		-	1	1.5	
$V_{\rm R}$ = 0 V, <i>f</i> = 1 MHz, for Application example 4		-	0.5	0.75	
Series inductance (per diode)	LS				nH
SOT323		-	1.4	-	
SOT363		-	1.6	-	

¹V_{ESD} according to IEC61000-4-2, only valid in anti-parallel or rail-to-rail connection.

Please refer to the application examples.

 $^{2}I_{\text{DD}}$ according to IEC61000-4-5, only valid in anti-parallel or rail-to-rail connection.

Please refer to the application examples.

³Only valid in rail-to-rail configuration $V_{CC} \ge V_{RWM}$

⁴Total capacitance line to ground (2 diodes in parallel)



Forward clamping voltage $V_{FC} = f(I_{PP})$

 $t_{\rm p}$ = 8 / 20 µs



Forward current $I_{\rm F}$ = $f(V_{\rm F})$

T_A = Parameter

in anti-parallel configuration



Reverse current $I_{R} = f(V_{R})$

 T_A = Parameter

in rail-to-rail configuration



Line capacitance $C_{T} = f$ (f) $V_{R} = 0 V$



=





Insertion loss $|S_{21}|^2 = f(f)$ $V_R = 0$ V, line to ground, Z = 50 Ω

-0.25-0.375-0.5-0.625-0.625-0.750 250 500 750 1000 1250 1500 MHz 2000

4



1. Application example ESD1P0RFW

1 channel, anti-parallel configuration



2. Application example ESD1P0RFW

1 channel, rail-to-rail configuration





3. Application example ESD1P0RFS

2 channel, anti-parallel configuration



Pins 1, 2 and 4, 5 should be connected in parallel directly to a ground plane on the board. Clamped input voltage at I/O port is limited to \pm VCL (clamping voltage) at positive resp. negative transients.

Line capacitance to ground = 1.0 pF

4. Application example ESD1P0RFS 1 channel, low capacitance anti-parallel configuration



Pins 1 and 5 should be connected directly to a ground plane on the board. Pins 3, 6 are not connected. Clamped input voltage at I/O port is limited to +- 2 x VCL (clamping voltage) at positive resp. negative transients.

RF line on PCB





Foot Print



Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel







Foot Print



Marking Layout (Example)

Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.





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